

#### **Features**

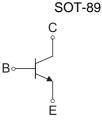
Collector-Emitter Voltage: V<sub>CEO</sub> = 12V
 Collector Power Dissipation: Pc = 1.2W
 Collector Current -Continuous: Ic = 100mA

# 1. BASE 2. COLLECTOR

# **Package Marking and Ordering Information**

Product ID Pack		Marking	Qty(PCS)	
H2SC3357	SOT-89	RF/RE	1000	





# Maxmim Ratings (Ta=25 unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	20	V
V <sub>CEO</sub>	Collector-Emitter Voltage	12	V
V <sub>EBO</sub>	Emitter-Base Voltage	3	V
Ic	Collector Current -Continuous	100	mA
Pc	Collector Power Dissipation	1.2	W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}$ C

# Electrcal Charcteristics (Ta=25 unless otherwise specified)

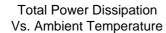
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100 μA , I <sub>E</sub> =0	20			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> *	I <sub>C</sub> = 1mA, I <sub>B</sub> =0	12			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 100 μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =20V, I <sub>E</sub> =0			1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =1V, I <sub>C</sub> =0			1	μΑ
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =20mA	50		250	
Insertion Power Gain	S21e  <sup>2</sup>	V <sub>CE</sub> =10V, I <sub>C</sub> =20mA,f=1GHz		9	0.4	
Noise Figure	NF	V <sub>CE</sub> =10V, I <sub>C</sub> =7mA,f=1GHz	6.5	1.1		dB
Noise rigure	INI	V <sub>CB</sub> =10V,I <sub>C</sub> =40mA,f=1GHz		1.8	3	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50m A, I <sub>B</sub> =5mA			0.4	V
Base -emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =50m A, I <sub>B</sub> =5mA			1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =20mA		6.5		GHz
Reverse Transfer Capacitance	C <sub>re</sub>	V <sub>CB</sub> =10V,I <sub>E</sub> =0,f=1MHz			1	pF

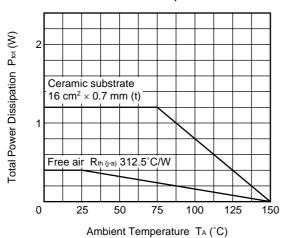
<sup>\*</sup>pulse test

#### **Classifiction Of hFE**

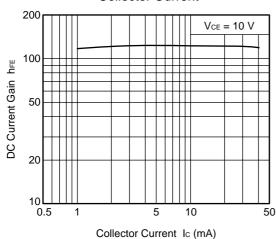
Rank	H2SC3357 RF	H2SC3357 RE		
Range	82 -160	120 - 270		
Marking	RF	RE		

#### **Typical Characteristics**

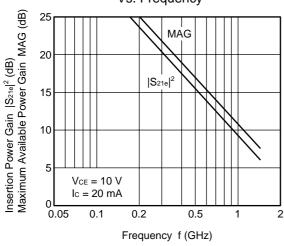




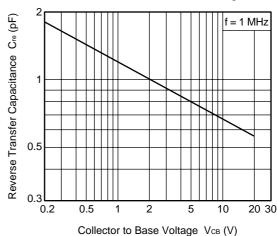
#### DC Current Gain Vs Collector Current



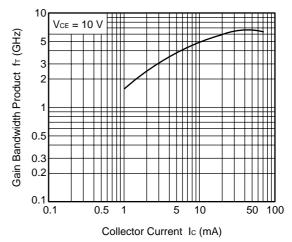
Insertion Power Gain,MAG Vs. Frequency



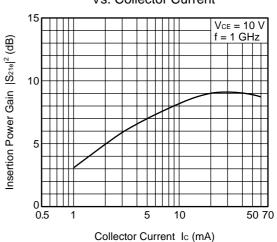
Reverse Transfer Capacitance Vs. Collector To Base Voltage



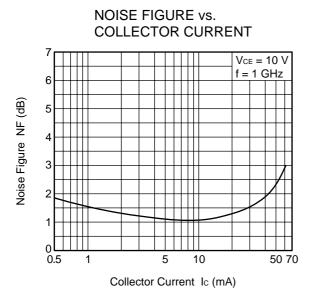
Gain Bandwidth Prouct Vs. Collector CUrrent

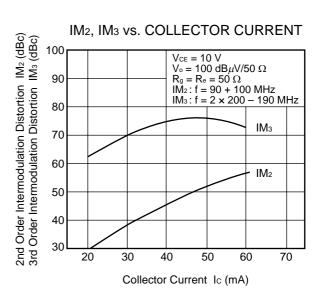


Insertion Power Gain Vs. Collector Current

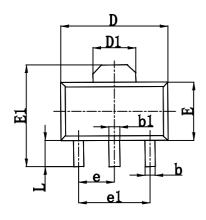


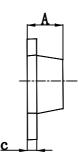






# **SOT-89 Package Outline Dimensions**





Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550 REF.		0.061 REF.		
E	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP.		0.060 TYP.		
e1	3.000 TYP.		0.118 TYP.		
L	0.900	1.200	0.035	0.047	



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